

IN THE CLAIMS

Please amend the claims as follows:

Claims 1-5 (Canceled).

Claim 6 (New): A semiconductor device comprising:

an inductor provided with a conductor interconnection formed spirally on a semiconductor substrate; and

a shield that is provided with a conductor interconnection in a ring having a continuous configuration provided along an outer periphery of the spiral pattern of the inductor with opening a portion of the conductor interconnection, and that is electrically connected to ground potential.

Claim 7 (New): A semiconductor device according to Claim 6, wherein an interconnection width of the shield is equal to or more than a size of a spacing of the spiral pattern of the inductor, and is equal to or less than a radius of the spiral pattern of the inductor.

Claim 8 (New): A semiconductor device according to Claim 6, wherein a distance between the shield and an outer border of the interconnection of the inductor is equal to a spacing of the spiral pattern of the inductor.

Claim 9 (New): A semiconductor device according to Claim 6, further comprising:
a plurality of interconnection layers formed on the semiconductor substrate, wherein the inductor is formed in any one of these interconnection layers; and the shield is formed in

a different interconnection layer from the interconnection layer in which the inductor is formed.

Claim 10 (New): A semiconductor device comprising:

an inductor provided with a conductor interconnection formed spirally on a semiconductor substrate; and

a shield that is provided with a conductor interconnection in a ring having a continuous configuration provided along an inner periphery of the spiral pattern of the inductor with opening a portion of the conductor interconnection, and that is electrically connected to ground potential.

Claim 11 (New): A semiconductor device according to Claim 10, wherein an interconnection width of the shield is equal to or less than a size of an interconnection width of the inductor.